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Comparative study on in-situ surface cleaning effect of intrinsic oxide covering GaAs surface using TMA precursor and Al_2O_3 buffer layer for HfGdO gate dielectrics

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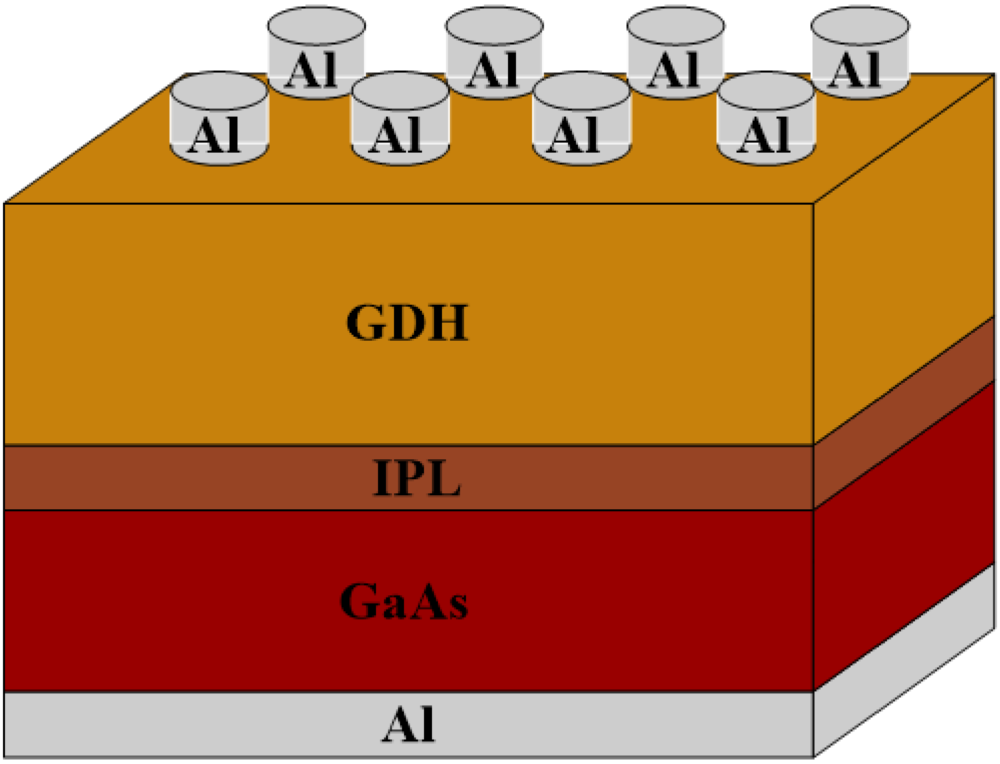

Fig. S1 The Schematic diagram of Al/GDH/IPL/GaAs/Al MOS capacitor device structure.